

GLASPER et al
Appl. No. 10/520,850
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AMENDMENTS TO THE SPECIFICATION:

Page 2, amend the paragraph beginning at line 22 and continuing to page 3, line 6 as follows:

US Published Application No. 2002/0024058A1, now U.S. Patent 6,858,912, discloses a photodetector circuit including a photodiode detector and associated readout CMOS circuitry, in which an active region of the photodiode detector is formed by at least one epitaxial layer, and a guard ring is provided to delimit the photodiode detector in order to enhance electrical field uniformity and inhibit premature breakdown. The provision of the epitaxial layer provides a number of improvements in photodiode characteristics combined with the low cost of CMOS technology, whilst the guard ring reduces the scope for localised high electric fields and improves breakdown characteristics. The CMOS component may be a substrate and CMOS circuitry supported by and insulated from the substrate, and the photodiode detector may be operable in a current multiplication mode and comprise at least one region epitaxially deposited upon the substrate. The photodiode detector may be a PIN structure, or an avalanche photodiode comprising a first region of one conductivity type incorporated in the substrate, a second region of opposite conductivity type being provided by the epitaxial layer.

Page 6, amend the paragraph beginning at line 12 as follows:

Figure 1 (Prior Art) is an explanatory sectional view of the structure of a known avalanche photodiode;